

Title (en)  
Semiconductor device and method for manufacturing the same

Title (de)  
Halbleitervorrichtung und Herstellungsverfahren dazu

Title (fr)  
Dispositif semiconducteur et procédé de fabrication

Publication  
**EP 1575093 B1 20081001 (EN)**

Application  
**EP 05250878 A 20050216**

Priority  
JP 2004038909 A 20040216

Abstract (en)  
[origin: EP1575093A2] A semiconductor device includes a semiconductor substrate (100), an isolation film (4) that is provided in one principal surface of the semiconductor substrate, wiring (1) that is arranged on the isolation film, a diffusion layer (16) that is formed inside the semiconductor substrate and located in the vicinity of the isolation film, and an insulating film (8) that covers the diffusion layer (16) over the one principal surface of the semiconductor substrate (100). The insulating film further covers a portion of the isolation film (4) near to the diffusion layer and comes into contact with the side of the wiring (1) near to the diffusion layer.

IPC 8 full level  
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CPC (source: EP KR US)  
**B32B 5/16** (2013.01 - KR); **B32B 7/12** (2013.01 - KR); **B32B 17/068** (2013.01 - KR); **B32B 27/14** (2013.01 - KR); **C09J 11/00** (2013.01 - KR); **C09J 133/00** (2013.01 - KR); **C09J 175/04** (2013.01 - KR); **H01L 21/823443** (2013.01 - EP US); **H01L 21/823456** (2013.01 - EP US); **H01L 21/823468** (2013.01 - EP US); **H01L 21/823475** (2013.01 - EP US); **H01L 27/146** (2013.01 - EP US); **B32B 2307/412** (2013.01 - KR)

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